

Error		Corrections		Time Stamp		DBs		Search Text		Hits		L #		Type	
Errors		Information													
0				2000/09/21	16:47	USPAT		((silicon adj on adj insulat\$3) SOI)		3573		L3		BRS	
0				2000/09/21	16:47	USPAT		3 and bond\$3		1418		L4		BRS	
0				2000/09/21	16:48	USPAT		3 and join\$3		525		L5		BRS	
0				2000/09/21	16:49	USPAT		4 5		1670		L7		BRS	
0				2000/09/21	16:53	USPAT		7 and (oxidiz\$3)		761		L8		BRS	
0				2000/09/21	16:55	USPAT		8 and (mono adj crystal\$6 adj silicon)		3		L9		BRS	
0				2000/09/21	16:57	USPAT		8 and (implant\$3 dop\$4)		647		L10		BRS	
0				2000/09/21	19:44	USPAT		10 and (substrate with oxidiz\$3)		330		L11		BRS	

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Computer: WS11378

Date: 09/21/2000

Time: 20:40

		E r r o r s		C o n f i d e n t i a l	
Type	Hits	Search Text	DBs	Time Stamp	
1 BRS	444663	substrate semiconductor wafer	USPAT	2000/09/14 11:00	0
2 BRS	128507	(substrate semiconductor wafer) and (insulat\$3)	USPAT	2000/09/14 11:07	0
3 BRS	0	1 and (dielectric)	USPAT	2000/09/14 11:07	0
4 BRS	239704	(substrate semiconductor wafer) and (dielectric insulat\$3 oxide)	USPAT	2000/09/14 13:50	0
5 BRS	24527	((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and polysilicon	USPAT	2000/09/14 13:51	0
6 BRS	7758	((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and (single adj crystal\$6 adj silicon)	USPAT	2000/09/14 13:55	0
7 BRS	33	((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and (mono adj crystal\$3 adj silicon)	USPAT	2000/09/14 14:00	0
8 BRS	10877	((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and (amorphous adj silicon)	USPAT	2000/09/14 14:01	0

Errors		Error Information		Time Stamp	DBs	Search Text	Hits	Type	
	9	BRS	35125	USPAT 2000/09/14 14:02		((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and (amorphous adj silicon)) ((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and (mono adj crystal\$3 adj silicon)) ((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and (single adj crystal\$6 adj silicon)) ((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and polysilicon)			
	10	BRS	14046	USPAT 2000/09/14 14:04		((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and (amorphous adj silicon)) ((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and (mono adj crystal\$3 adj silicon)) ((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and (single adj crystal\$6 adj silicon)) ((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and polysilicon) and implant\$3			0

		Type	Hits	Search Text	DBs	Time Stamp	Error Counts		Error Counts
11	BRS	13	((((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and (amorphous adj silicon)) (((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and (mono adj crystal\$3 adj silicon)) (((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and (single adj crystal\$6 adj silicon)) (((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and polysilicon)) and implant\$3) and ((non adj dopant) nondopant)				USPAT	2000/09/14 14:05	0

Errors		Error Information		Time Stamp	DBs	Search Text	Hits	Type	
0				2000/09/14 14:21	USPAT	(((((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and (amorphous adj silicon)) (((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and (mono adj crystal\$3 adj silicon)) (((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and (single adj crystal\$6 adj silicon)) (((substrate semiconductor wafer) and (dielectric insulat\$3 oxide)) and polysilicon)) and implant\$3) and ((non adj dopant) nondopant)) and ((dop\$3 implant\$3) same nitrogen)	8	BRS	13
0				2000/09/14 14:24	USPAT	((("438/147") or ("438/165") or ("438/168") or ("438/197") or ("438/225") or ("438/216") or ("438/211") or ("438/217") or ("438/249") or ("438/279") or ("438/282") or ("438/289") or ("438/298") or ("438/319") or ("438/412") or ("438/406") or ("438/407")).CCLS.	1418	IS&R	14